



Single Phase Diode Bridges QL60-QL100



Features

- Current:5-300A,Voltage:100-1600V
- All models feature the same compact dimensions to Provide auniform mounting pitch
- Glass passivated diode chip
- Excellent power/volume ratio,High thermal conductivity Package, electrically insulated case

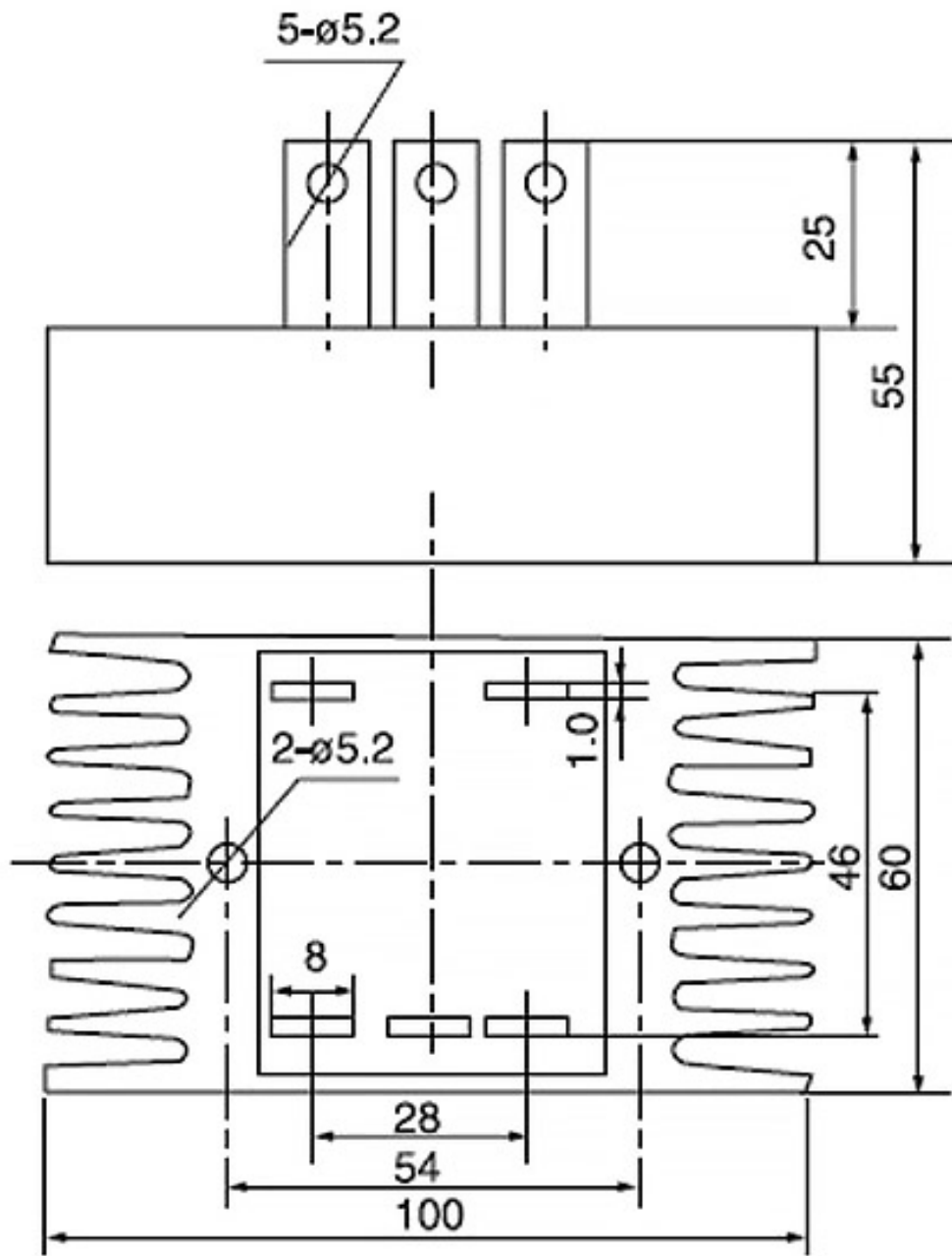
$V_{RRM} = 100-1600\text{ V}$
 $I_D = 60-100\text{ A}$
 $V_F = 1.1\text{ V}$
 $I_{FSM} = 400\text{ A}$

Typical Applications

- Eliminator supply,industrial automatic control
- Numierial-controlled machinery,telecontrol system

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	VALUE		UNIT
			Min	Max	
I_D	Output current	180° sine wave, 50HZ	60	100	A
V_{RRM}	Repetitive peak reverse voltage	$V_{DRM}\&V_{RRM}\ tp=10ms$ $V_{DSM}\&V_{RSM}=V_{DRM}\&V_{RRM}+100V$	100	1600	V
V_{RMS}	RMS current		70	860	V
V_{DC}	DC blocking voltage		100	1600	V
I_{FSM}	Surge on-state current	sine wave		400	A
V_F	Diode forward voltage	$I_F=17.5A$		1.1	V
I_R	Reverse leakage current	$T_a=25^\circ C$		10	uA
$I_{R(H)}$		$T_a=100^\circ C$		200	uA
$R_{th(j-c)}$	Thermal impedance node to the shell	180° sine wave, single heat sink		5.0	°C/W
$R_{th(c-a)}$	Thermal impedance (shell to powder)	180° sine wave, single heat sink		8	°C/W
V_{iso}	Insulation voltage		2500		V
T_J	Stored temperature		-40	125	°C
T_{stq}	Stored temperature		-40	150	°C
W_t	Weight			315	g

DIMENSIONS



TOPOLOGY OF INTERNAL CONNECTION

